

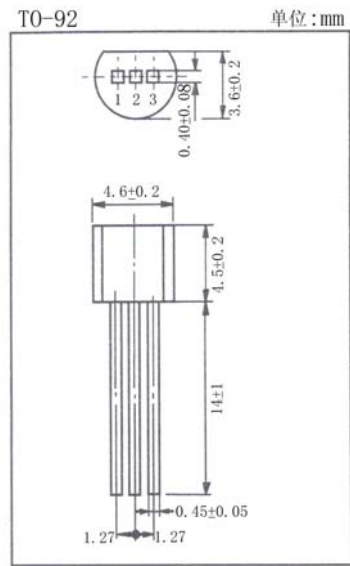
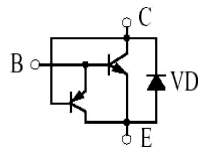
MJE13003DI1 (3DD13003DI1)硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途：主要用于节能灯、日光灯电子镇流器及其它开关、振荡电路。

Purpose: High frequency electronic lighting ballast applications, converters, inverters, switching regulators, etc.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	600	V
V _{CE0}	400	V
V _{EB0}	9.0	V
I _C	1.5	A
P _C (Ta=25℃)	1.0	W
T _j	150	℃
T _{stg}	-55~150	℃



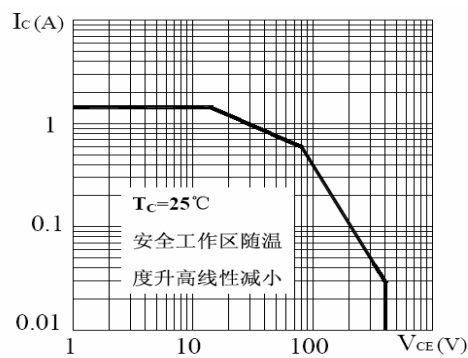
引脚：1. E 2. C 3. B

电性能参数/Electrical characteristics(Ta=25℃)

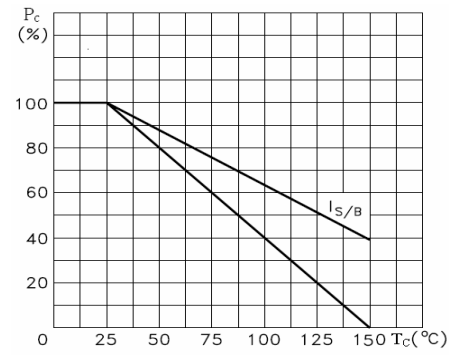
参数符号 Symbol	测试条件 Test condition	数值 Rating			单位 Unit
		最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =1mA I _E =0	600			V
V _{CE0}	I _C =10mA I _B =0	400			V
V _{EB0}	I _E =1mA I _C =0	9.0			V
I _{CB0}	V _{CB} =600V I _E =0			0.1	mA
I _{CE0}	V _{CE} =400V I _B =0			0.1	mA
I _{EB0}	V _{EB} =9.0V I _C =0			0.1	mA
h _{FE}	V _{CE} =5.0V I _C =200mA	10		40	
V _{CE(sat)}	I _C =1A I _B =250mA			0.8	V
V _{BE(sat)}	I _C =1A I _B =250mA			1.2	V
f _T	V _{CE} =10V I _C =100mA f=1.0MHz	5.0			MHz
t _f	V _{CE} =5V I _C =250mA (UI9600)			0.6	μs
t _S				3.5	μs

MJE13003DI1 (3DD13003DI1)

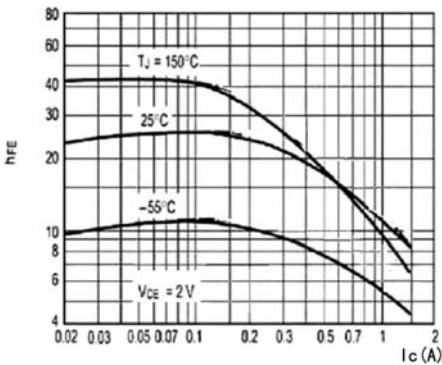
SOA (DC)



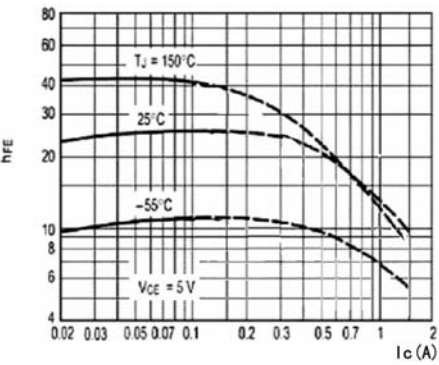
P_c-T_c



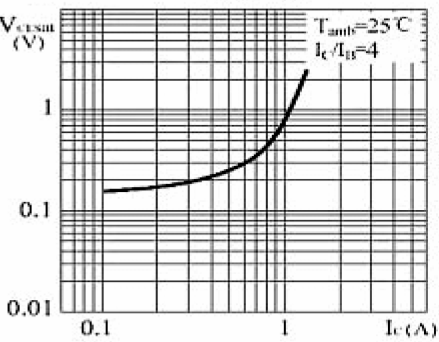
$h_{FE}-I_c$



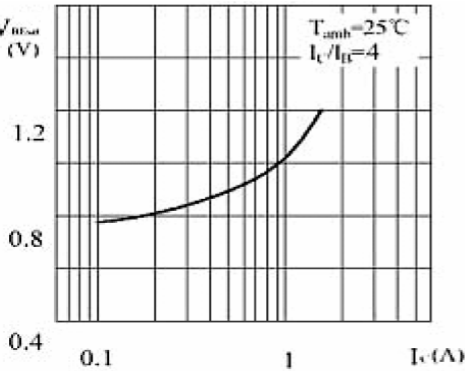
$h_{FE}-I_c$



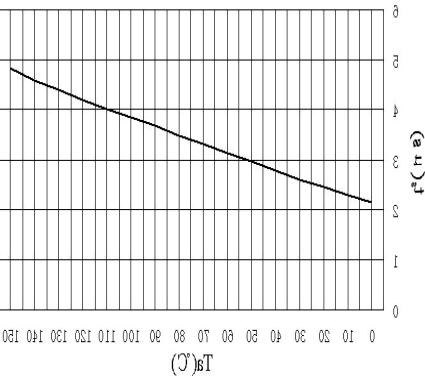
$V_{ces}-I_c$



$V_{bes}-I_c$



t_s-T_a



$h_{FE}-T_a$

